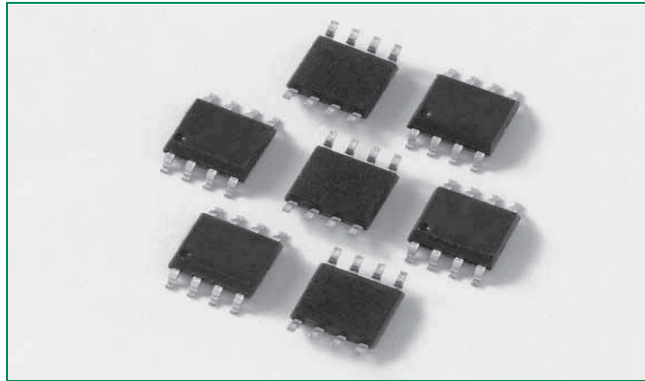
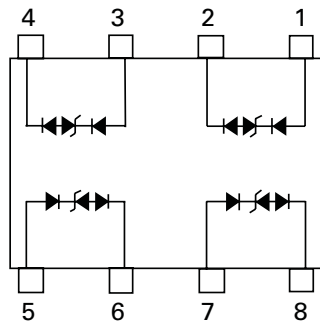


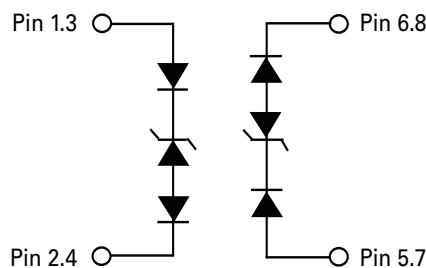
SPLV2.8-4 Series 2.8V 40A TVS Array



Pinout



Functional Block Diagram



NOT RECOMMENDED FOR NEW DESIGNS

SPLV2.8-4BTG is eventually going to be replaced by the *SLVU2.8-4BTG* TVS Diode Array with identical form, fit, and function. Please use this device for new or future designs and more detail can be found on Littelfuse.com [Description](#)

GREEN

The SPLV2.8-4 was designed to protect low voltage, CMOS devices from ESD and lightning induced transients. There is a compensating diode in series with each low voltage TVS to present a low loading capacitance to the line being protected. These robust structures can safely absorb repetitive ESD strikes at $\pm 30\text{kV}$ (contact discharge) per IEC61000-4-2 standard and each structure can safely dissipate up to 40A (IEC61000-4-5, $t_p=8/20\mu\text{s}$) with very low clamping voltages.

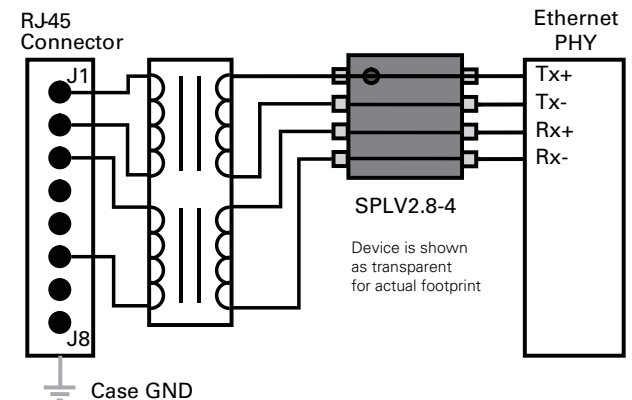
Features

- ESD, IEC61000-4-2, $\pm 30\text{kV}$ contact, $\pm 30\text{kV}$ air
- EFT, IEC61000-4-4, 40A (5/50ns)
- Lightning, IEC61000-4-5, 40A (8/20 μs)
- Low capacitance of 2pF per line
- Low leakage current of $1\mu\text{A}$ (MAX) at 2.8V
- SOIC-8 pin (JEDEC MS-012) configuration allows for simple flow-through layout

Applications

- 10/100/1000 Ethernet
- WAN/LAN Equipment
- Switching Systems
- Desktops, Servers, and Notebooks
- Analog Inputs
- Base Stations

Application Example



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Electrical Characteristics ($T_{OP} = 25^{\circ}\text{C}$)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Reverse Standoff Voltage	V_{RWM}	$I_R \leq 1\mu\text{A}$			2.8	V
Reverse Breakdown Voltage	V_{BR}	$I_T = 2\mu\text{A}$	3.0			V
Snap Back Voltage	V_{SB}	$I_T = 50\text{mA}$	2.8			V
Reverse Leakage Current	I_{LEAK}	$V_R = 2.8\text{V}$ (Each Line)			1	μA
Clamping Voltage ¹	V_C	$I_{PP} = 5\text{A}$, $t_p = 8/20\mu\text{s}$ (Each Line)		7.0	8.5	V
Clamping Voltage ¹	V_C	$I_{PP} = 24\text{A}$, $t_p = 8/20\mu\text{s}$ (Each Line)		13.9	15.0	V
ESD Withstand Voltage ¹	V_{ESD}	IEC61000-4-2 (Contact)	± 30			kV
		IEC61000-4-2 (Air)	± 30			kV
Dynamic Resistance	R_{DYN}	$(V_{C2} - V_{C1}) / (I_{PP2} - I_{PP1})$ (Each Line)		0.4		Ω
Diode Capacitance ¹	C_D	$V_R = 0\text{V}$, $f = 1\text{MHz}$ (Each Line)		2.0	2.5	pF

Note: ¹Parameter is guaranteed by design and/or device characterization.

Absolute Maximum Ratings

Parameter	Rating	Units
Peak Pulse Power ($t_p = 8/20\mu\text{s}$)	600	W
Peak Pulse Current ($t_p = 8/20\mu\text{s}$)	40	A
Operating Temperature	-40 to 85	$^{\circ}\text{C}$
Storage Temperature	-60 to 150	$^{\circ}\text{C}$

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Figure 1: Capacitance vs. Reverse Voltage

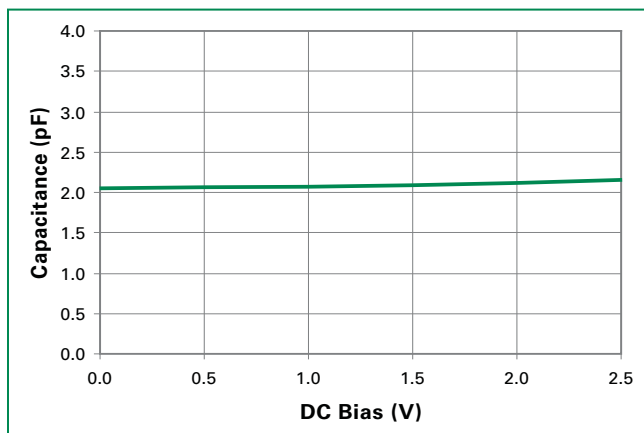


Figure 2: Clamping Voltage vs. I_{PP}

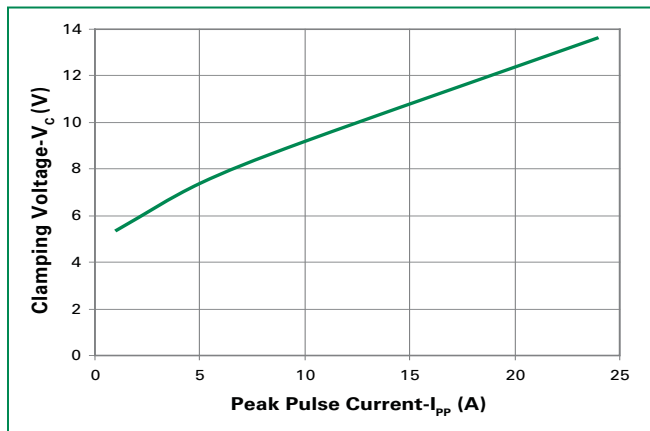
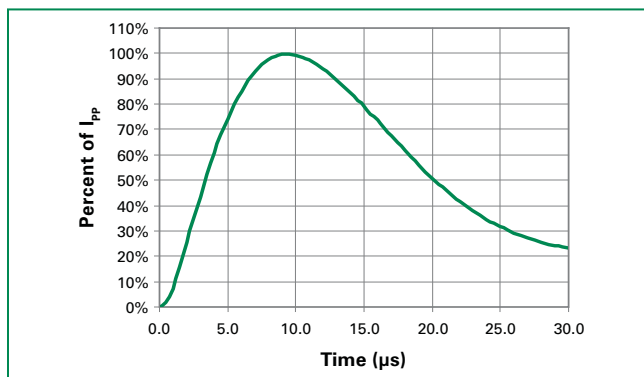


Figure 3: Pulse Waveform



Product Characteristics

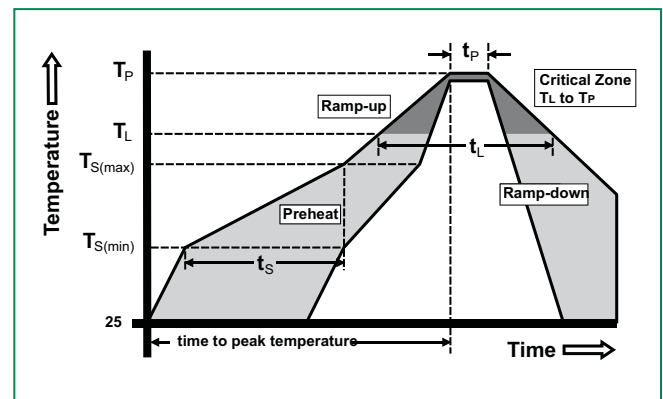
Lead Plating	Matte Tin
Lead Material	Copper Alloy
Lead Coplanarity	0.0004 inches (0.102mm)
Substitute Material	Silicon
Body Material	Molded Epoxy
Flammability	UL 94 V-0

Notes :

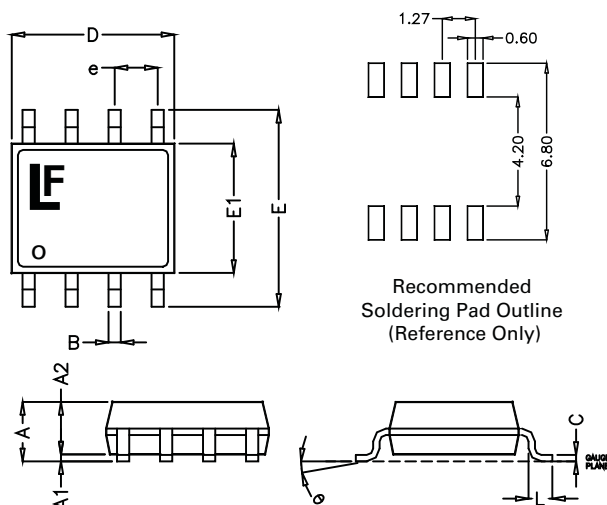
1. All dimensions are in millimeters
2. Dimensions include solder plating.
3. Dimensions are exclusive of mold flash & metal burr.
4. Blo is facing up for mold and facing down for trim/form, i.e. reverse trim/form.
5. Package surface matte finish VDI 11-13.

Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 180 secs
Average ramp up rate (Liquidus) Temp (T_L) to peak		5°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_p)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		260°C



Package Dimensions — Mechanical Drawings and Recommended Solder Pad Outline



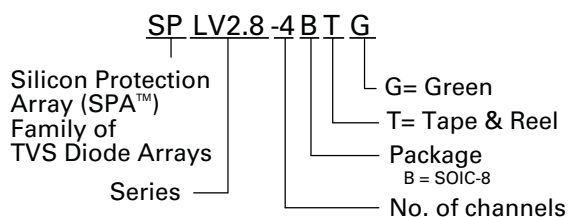
Package	SOIC			
Pins	8			
JEDEC	MS-012			
	Millimetres		Inches	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A1	0.10	0.25	0.004	0.010
A2	1.25	1.65	0.050	0.065
B	0.31	0.51	0.012	0.020
c	0.17	0.25	0.007	0.010
D	4.80	5.00	0.189	0.197
E	5.80	6.20	0.228	0.244
E1	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
L	0.40	1.27	0.016	0.050

SPLV2.8-4 Series

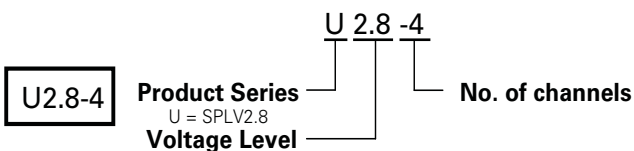
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Part Numbering System



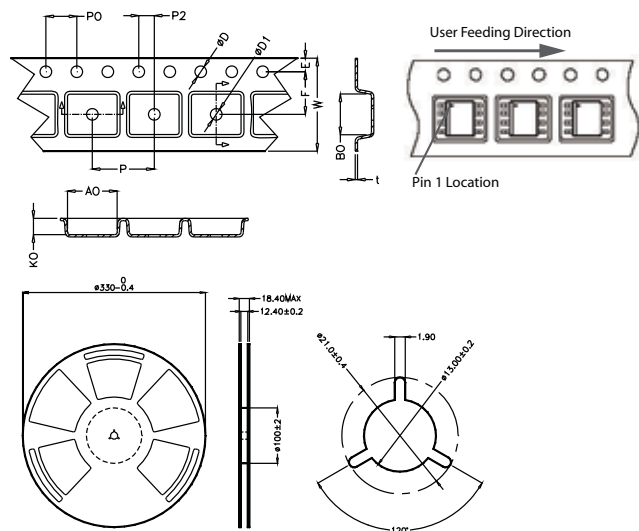
Part Marking System



Ordering Information

Part Number	Package	Marking	Min. Order Qty.
SPLV2.8-4BTG	SOIC-8	U2.8-4	2500

Embossed Carrier Tape & Reel Specification — SOIC Package



Symbol	Millimetres		Inches	
	Min	Max	Min	Max
E	1.65	1.85	0.065	0.073
F	5.4	5.6	0.213	0.22
P2	1.95	2.05	0.077	0.081
D	1.5	1.6	0.059	0.063
D1	1.50 Min		0.059 Min	
P0	3.9	4.1	0.154	0.161
10P0	40.0 +/- 0.20		1.574 +/- 0.008	
W	11.9	12.1	0.468	0.476
P	7.9	8.1	0.311	0.319
A0	6.3	6.5	0.248	0.256
B0	5.1	5.3	0.2	0.209
K0	2	2.2	0.079	0.087
t	0.30 +/- 0.05		0.012 +/- 0.002	